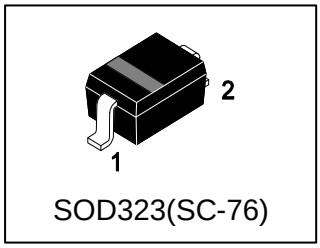
LBAS21HT1G
S-LBAS21HT1G

High Voltage Switching Diode



1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
LBAS21HT1G	JS	3000/Tape&Reel
LBAS21HT3G	JS	10000/Tape&Reel

3. MAXIMUM RATINGS(Ta = 25ºC)

Parameter	Symbol	Limits	Unit
Continuous Reverse Voltage	VR	250	V
Peak Forward Current	IF	200	mA
Repetitive Peak Forward Surge Current (tp=1ms, δ=0.25)	IFRM	625	mA
Non-Repetitive Peak Forward Surge Current (tp =1μs) (tp =100μs) (tp =10ms)	IFSM	 9 3 1.7	 A A A

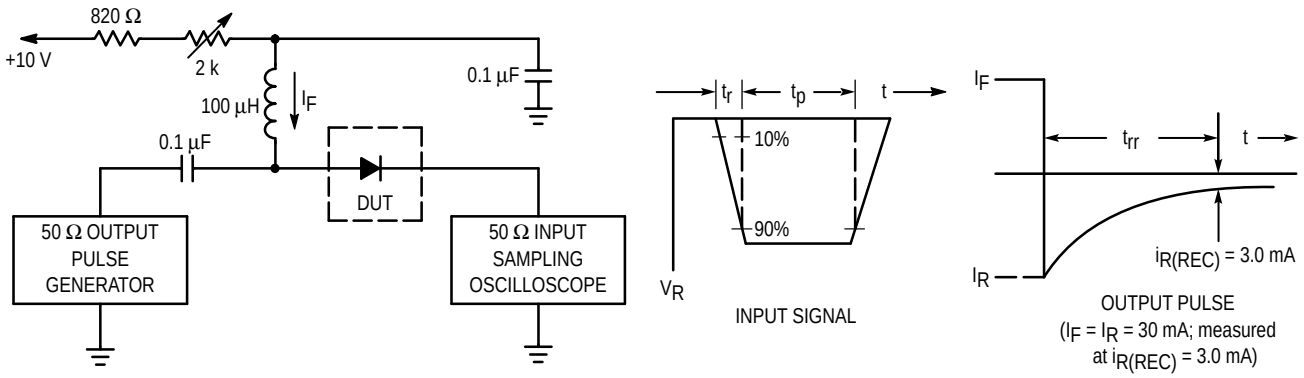
4. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation FR– 5 Board, (Note 1) TA = 25°C Derate above 25°C	PD	 200 1.57	 mW mW/℃
Thermal Resistance, Junction to Ambient	RθJA	635	℃/W
Junction and Storage Temperature Range	TJ , Tstg	-55~+150	℃

1. FR–5 Minimum Pad

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

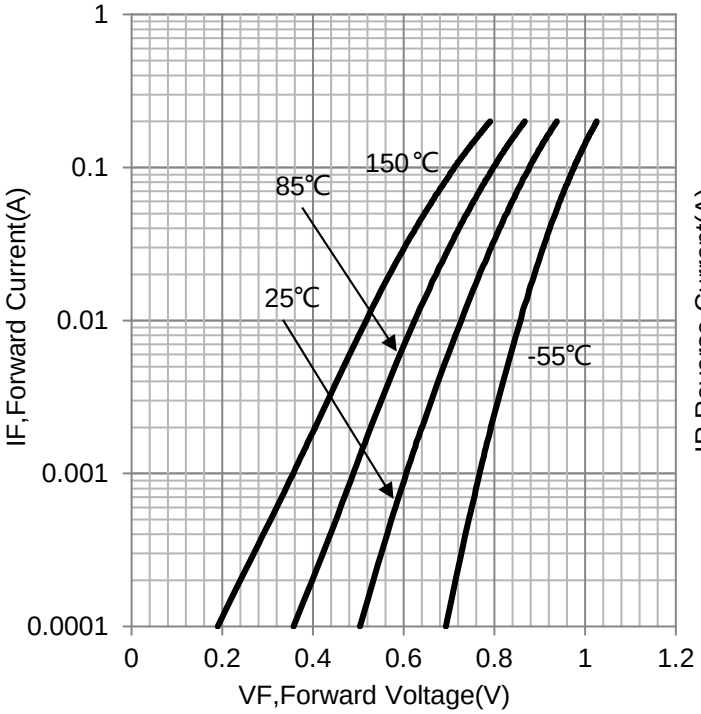
CHARACTERISTICS	Symbol	Min	Max	Unit
Reverse Voltage Leakage Current (VR=200V) (VR=200V, TJ = 150°C)	IR	 - -	 0.1 100	µA
Reverse Breakdown Voltage (IBR = 100 µA)	VBR	250	-	V
Forward voltage (IF =100mA) (IF =200mA)	VF	 - -	 1000 1250	mV
Diode capacitance (f=1MHz,VR =0)	Cd	-	5	pF
Reverse Recovery Time (IF = IR = 30mA, RL = 100Ω)	Trr	-	50	nS



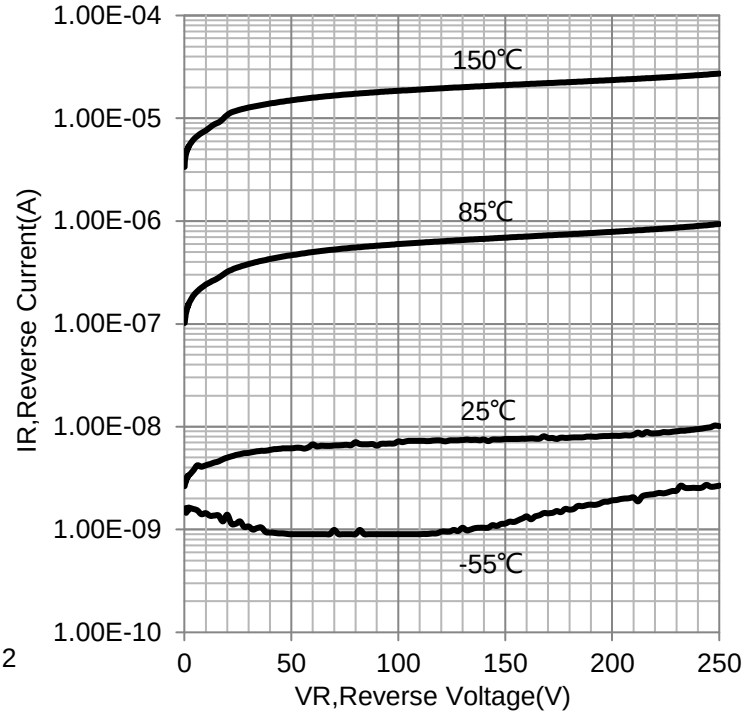
Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 30 mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 30 mA.
3. $t_p >> t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

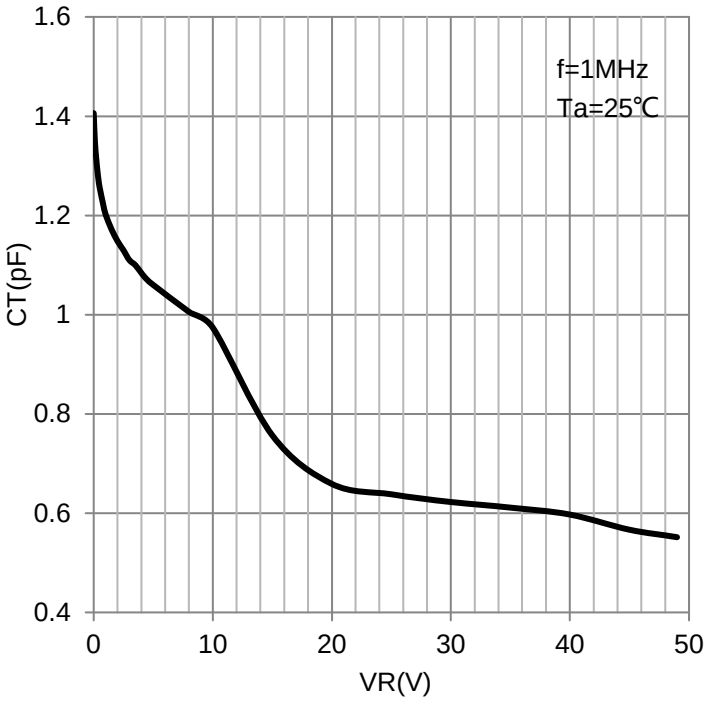
6.ELECTRICAL CHARACTERISTICS CURVES



IF vs. VF

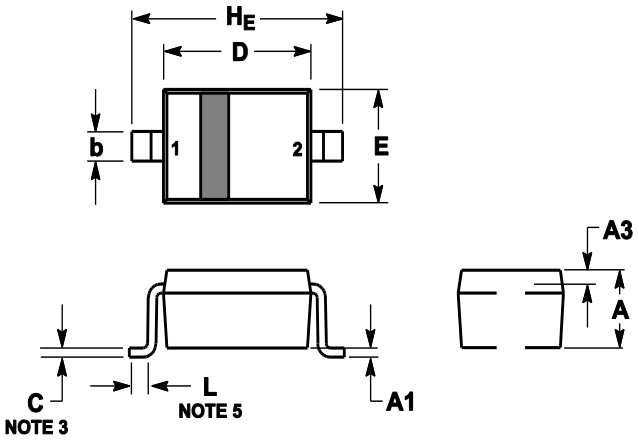


IR vs. VR



CT vs. VR

7.OUTLINE AND DIMENSIONS

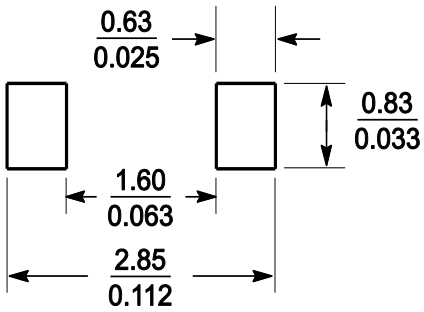


Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.8	0.9	1	0.031	0.035	0.04
A1	0	0.05	0.1	0	0.002	0.004
A3	0.15REF			0.006REF		
b	0.25	0.32	0.4	0.01	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.6	1.7	1.8	0.062	0.066	0.07
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
H_E	2.3	2.5	2.7	0.09	0.098	0.105

8.SOLDERING FOOTPRINT



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